New Jersey Semi-Conductor Products, Inc.

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1N4148

SILICON PLANAR DIODE

SILICON EPITAXIAL PLANAR DIODE

ONE PIECE GLASS-HERMETICALLY SEALED

ABSOLUTE MAXIMUM RATINGS

CHARACTERISTICS @ 25°C:		UNITS
Storage Temperature Range Lead Temperature 1/16 ± 1/32" from	65 to 200	°C
case for 10 sec	300	°C
Continuous Reverse Operating Voltage.	75	Volts
Power Dissipation	500	Wm
Derating Factor	2.85	MW/°C

45745.

- 1. PACKAGE CONTOUR OPTIONAL WITHIN A AND B. HERT SLURS, IF ANY, SHALL BE INCLUDED WITHIN THIS SYLINGER, BUT NOT SUBJECT TO THE MINIMUM LIMIT OF S.
- 2. LLAN GIAMETER NOT CONTROLLED IN ADMER TO ALLOW FOR FLASH, LLAD SINISH BUILDUP AND MINOR TRILEGU-LARITIES WITHER THAN HEAT SLUGS.
- POLABITY BENDY LD BY CATHOOL BAND.
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01/81	MIN	MAX	MIN	MAX
		5.63		
		7.70		
		0.56		
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h	25.40	10 10	1,000	1 566

ELECTRICAL CHARACTERISTICS @ 25°C unless otherwise noted

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CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	CONDITION
Peak Inverse Voltage	75			V	5μα
Peak Inverse Voltage	100			V	100μα
Forward Voltage			1.0	V	10mA
Reverse Current			25	na	20V
Reverse Current		150	50	μа	20V
Capacitance			4	pf	oV.
Reverse Recovery Time		Note 1	4	nsec	1mA

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.